

General Description

The 35N06B combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Features

- N-channel-Enhancement mode
- Lower On-resistance
- 100% Avalanche Tested
- RoHS Compliant

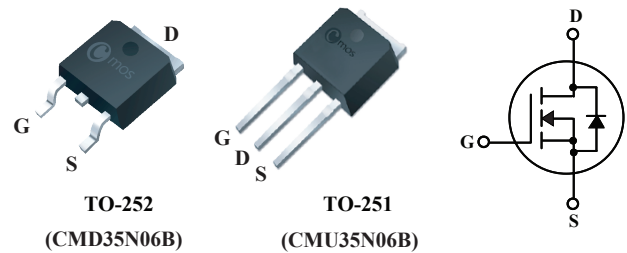
Product Summary

BVDSS	RDSON	ID
60V	36mΩ	30A

Applications

- DC-DC & DC-AC Converters
- DC Motor Drivers
- LED Lighting and LED Backlight Drivers

TO-252/251 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	30	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	20	A
I_{DM}	Pulsed Drain Current	120	A
EAS	Single Pulse Avalanche Energy ¹	24	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	40	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction -Case ¹	---	3.1	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=10A$	---	32	36	m Ω
		$V_{GS}=4.5V$, $I_D=5A$	---	37	42	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=60V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=10A$	---	13	---	S
R_g	Gate Resistance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.4	---	Ω
Q_g	Total Gate Charge	$V_{DS}=48V$, $V_{GS}=10V$, $I_D=20A$	---	15	---	nC
Q_{gs}	Gate-Source Charge		---	2.2	---	
Q_{gd}	Gate-Drain Charge		---	4.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=48V$, $V_{GS}=10V$, $R_G=2.5\Omega$ $I_D=20A$	---	7	---	ns
T_r	Rise Time		---	13	---	
$T_{d(off)}$	Turn-Off Delay Time		---	18	---	
T_f	Fall Time		---	2.5	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	670	---	pF
C_{oss}	Output Capacitance		---	40	---	
C_{rss}	Reverse Transfer Capacitance		---	30	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	30	A
I_{SM}	Pulsed Source Current		---	---	120	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=10A$, $T_J=25^{\circ}\text{C}$	---	0.88	1.3	V

Note :

1.The EAS data shows Max. rating . The test condition is $V_{DD}=30V$, $V_{GS}=10V$, $L=1\text{mH}$, $I_{AS}=7A$.

This product has been designed and qualified for the consumer market.

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Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

